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Kind regards,

Team Nexperia

PDTA123Y series

PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 10 k Ω

Rev. 04 — 3 September 2009

Product data sheet

1. Product profile

1.1 General description

PNP Resistor-Equipped Transistors (RET).

Table 1. Product overview

Type number	Package	Package			
	NXP	JEITA	JEDEC	complement	
PDTA123YE	SOT416	SC-75	-	PDTC123YE	
PDTA123YK	SOT346	SC-59A	TO-236	PDTC123YK	
PDTA123YM	SOT883	SC-101	-	PDTC123YM	
PDTA123YS[1]	SOT54	SC-43A	TO-92	PDTC123YS	
PDTA123YT	SOT23	-	TO-236AB	PDTC123YT	
PDTA123YU	SOT323	SC-70	-	PDTC123YU	

^[1] Also available in SOT54A and SOT54 variant packages (see Section 2)

1.2 Features

- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs

1.3 Applications

- General purpose switching and amplification
- Inverter and interface circuits

Circuit drivers

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	-50	V
Io	output current (DC)		-	-	-100	mA
R1	bias resistor 1 (input)		1.54	2.2	2.86	kΩ
R2/R1	bias resistor ratio		3.6	4.5	5.5	



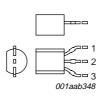
2. Pinning information

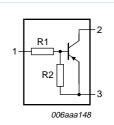
Table 3. Pinning

10010 01	9		
Pin	Description	Simplified outline Symbol	
SOT54			
1	input (base)		
2	output (collector)	R1	<u></u>
3	GND (emitter)	001aab347	3
		006	Saaa148

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30	ч	J	7	

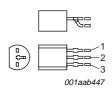
1	input (base)
2	output (collector)
3	GND (emitter)

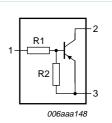




SOT54 variant

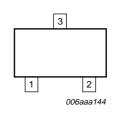
1	input (base)
2	output (collector)
3	GND (emitter)

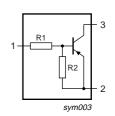




SOT23, SOT323, SOT346, SOT416

1	input (base)
2	GND (emitter)
3	output (collector)

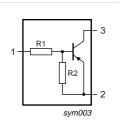




SOT883

1	input (base)
2	GND (emitter)
3	output (collector)





PDTA123Y_SER_4

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3. Ordering information

Table 4. Ordering information

Type number	Package					
	Name	Description	Version			
PDTA123YE	SC-75	plastic surface mounted package; 3 leads	SOT416			
PDTA123YK	SC-59A	plastic surface mounted package; 3 leads	SOT346			
PDTA123YM	SC-101	leadless ultra small plastic package; 3 solder lands; body 1.0 \times 0.6 \times 0.5 mm	SOT883			
PDTA123YS[1]	SC-43A	plastic single-ended leaded (through hole) package; 3 leads	SOT54			
PDTA123YT	-	plastic surface mounted package; 3 leads	SOT23			
PDTA123YU	SC-70	plastic surface mounted package; 3 leads	SOT323			

^[1] Also available in SOT54A and SOT54 variant packages (see Section 2 and Section 9)

4. Marking

Table 5. Marking codes

Table of Marking codes	
Type number	Marking code ^[1]
PDTA123YE	14
PDTA123YK	13
PDTA123YM	G2
PDTA123YS	TA123Y
PDTA123YT	*AD
PDTA123YU	*13

^[1] * = -: made in Hong Kong

^{* =} p: made in Hong Kong

^{* =} t: made in Malaysia

^{* =} W: made in China

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter	-	-50	V
V_{CEO}	collector-emitter voltage	open base	-	-50	V
V_{EBO}	emitter-base voltage	open collector	-	-5	V
VI	input voltage				
	positive		-	+5	V
	negative		-	-12	V
lo	output current (DC)		-	-100	mA
I _{CM}	peak collector current		-	-100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	SOT416		<u>[1]</u> _	150	mW
	SOT346		<u>[1]</u> _	250	mW
	SOT883		[2][3]	250	mW
	SOT54		[1] -	500	mW
	SOT23		[1] -	250	mW
	SOT323		<u>[1]</u> -	200	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C

^[1] Refer to standard mounting conditions.

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	SOT416		<u>[1]</u> _	-	833	K/W
	SOT346		<u>[1]</u> _	-	500	K/W
	SOT883		[2][3]	-	500	K/W
	SOT54		<u>[1]</u> _	-	250	K/W
	SOT23		<u>[1]</u> _	-	500	K/W
	SOT323		<u>[1]</u> _	-	625	K/W

^[1] Refer to standard mounting conditions.

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^[2] Reflow soldering is the only recommended soldering method.

^[3] Refer to SOT883 standard mounting conditions; FR4 printed-circuit board with 60 µm copper strip line.

^[2] Reflow soldering is the only recommended soldering method.

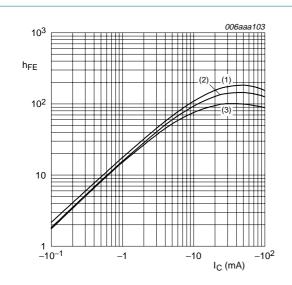
^[3] Refer to SOT883 standard mounting conditions; FR4 printed-circuit board with 60 µm copper strip line.

7. Characteristics

Table 8. Characteristics

T_{amb} = 25 °C unless otherwise specified

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}$	-	-	-100	nA
I _{CEO}	collector-emitter cut-off current	$V_{CE} = -30 \text{ V}; I_B = 0 \text{ A}$	-	-	-1	μΑ
		$V_{CE} = -30 \text{ V}; I_{B} = 0 \text{ A};$ $T_{j} = 150 \text{ °C}$	-	-	-50	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}$	-	-	-700	μΑ
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -5 \text{ mA}$	35	-	-	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}$	-	-	-150	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = -5 \text{ V}; I_{C} = -100 \mu\text{A}$	-	-0.75	-0.3	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = -300 \text{ mV}; I_C = -20 \text{ mA}$	-2.5	-1.15	-	V
R1	bias resistor 1 (input)		1.54	2.2	2.86	kΩ
R2/R1	bias resistor ratio		3.6	4.5	5.5	
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	-	2	pF



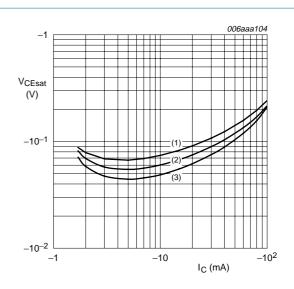
$$V_{CE} = -5 \text{ V}$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 1. DC current gain as a function of collector current; typical values



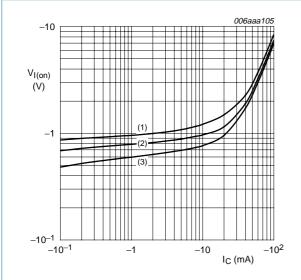
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 2. Collector-emitter saturation voltage as a function of collector current; typical values



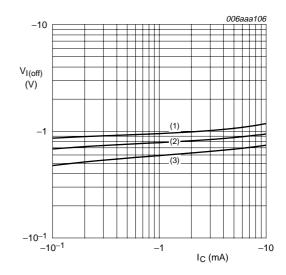
$$V_{CE} = -0.3 \text{ V}$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 3. On-state input voltage as a function of collector current; typical values



$$V_{CE} = -5 \text{ V}$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

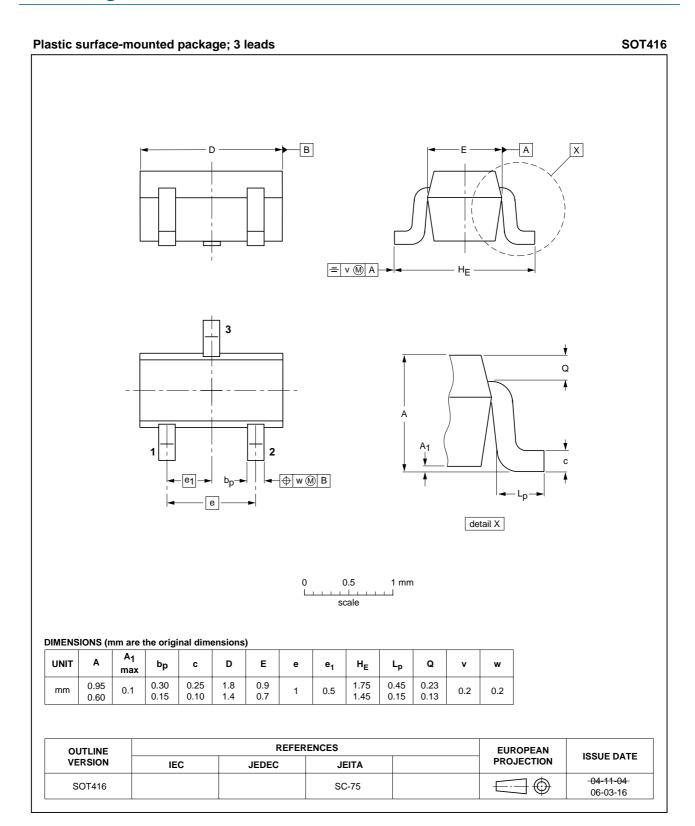
(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 4. Off-state input voltage as a function of collector current; typical values

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PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 10 k Ω

Package outline 8.



Package outline SOT416 (SC-75) Fig 5.

Product data sheet

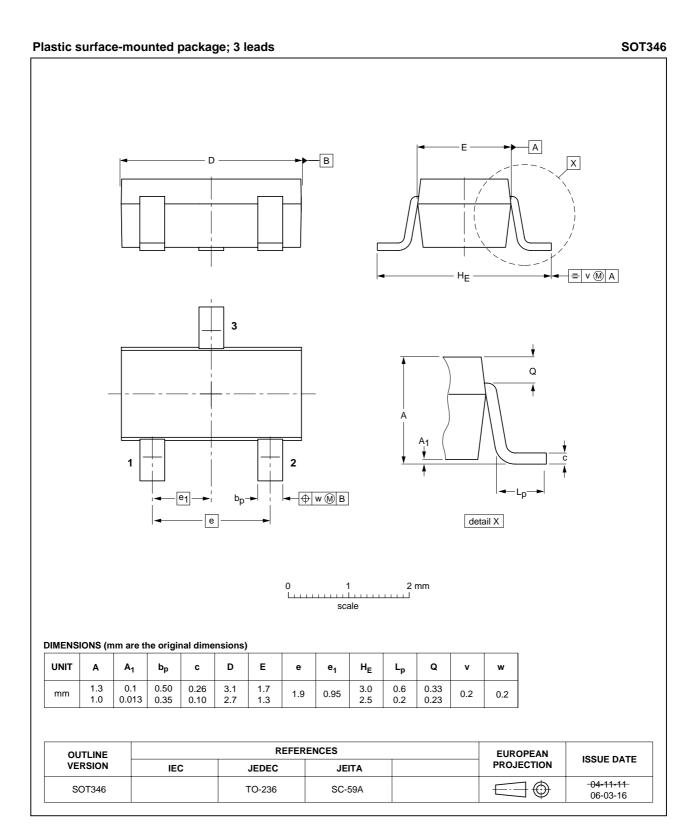
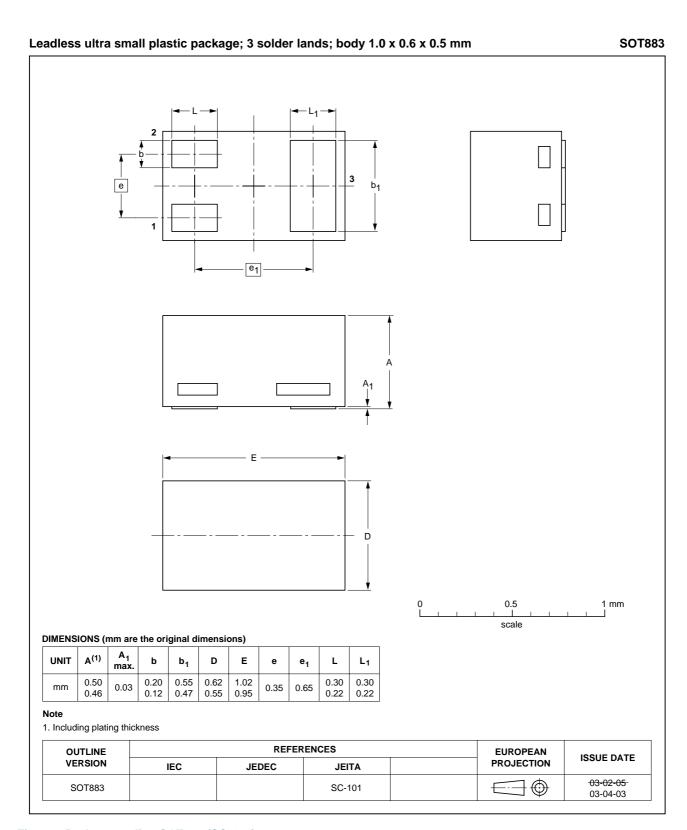


Fig 6. Package outline SOT346 (SC-59A/TO-236)

PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 10 k Ω



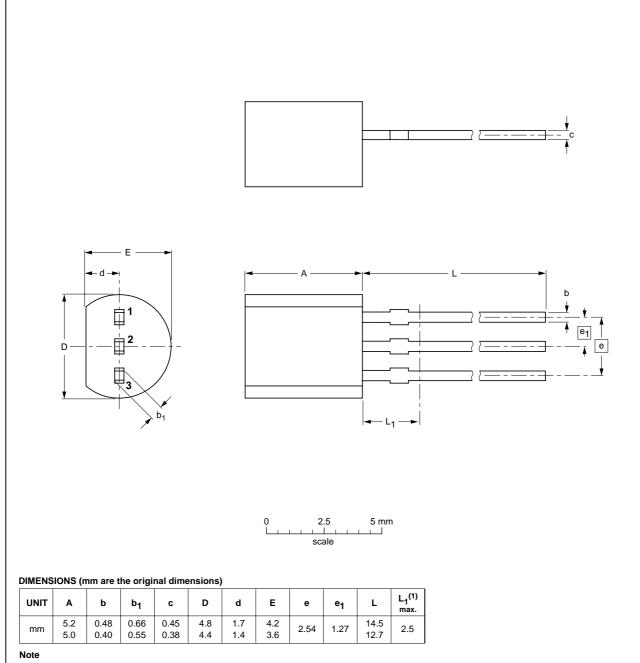
Package outline SOT883 (SC-101) Fig 7.

Product data sheet

Plastic single-ended leaded (through hole) package; 3 leads

SOT54

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1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE VERSION	REFERENCES				EUROPEAN	ISSUE DATE
	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT54		TO-92	SC-43A			04-06-28 04-11-16

Fig 8. Package outline SOT54 (SC-43A/TO-92)

Product data sheet

Plastic single-ended leaded (through hole) package; 3 leads (wide pitch)

SOT54A

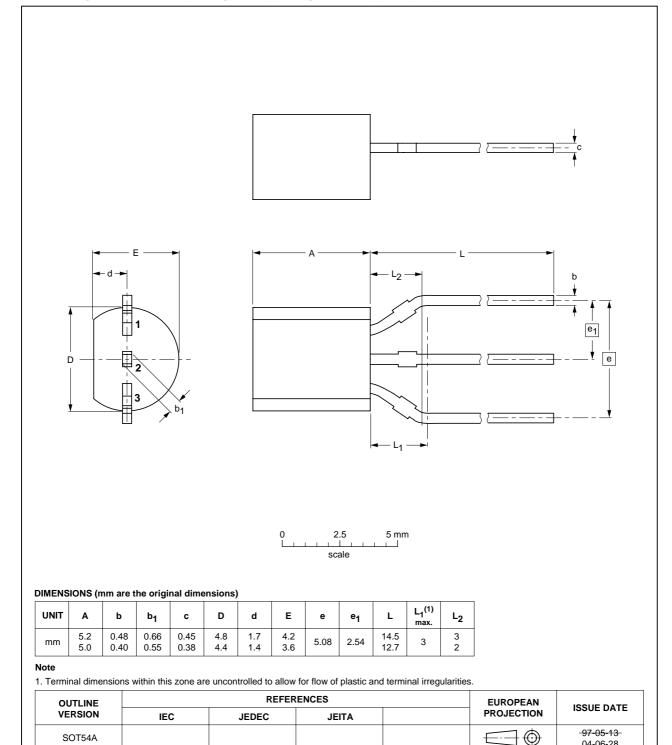


Fig 9. Package outline SOT54A

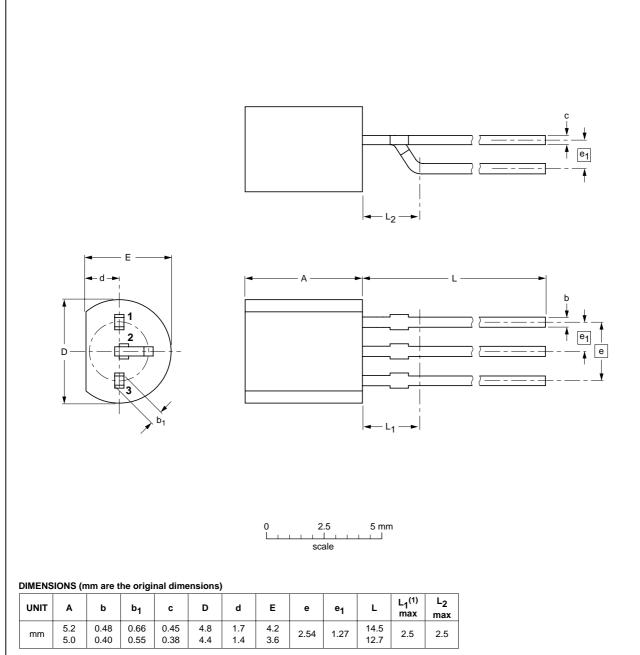
Product data sheet

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04-06-28

Plastic single-ended leaded (through hole) package; 3 leads (on-circle)

SOT54 variant



Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE VERSION	REFERENCES				EUROPEAN	ISSUE DATE	
	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT54 variant						-04-06-28 05-01-10	

Fig 10. Package outline SOT54 variant

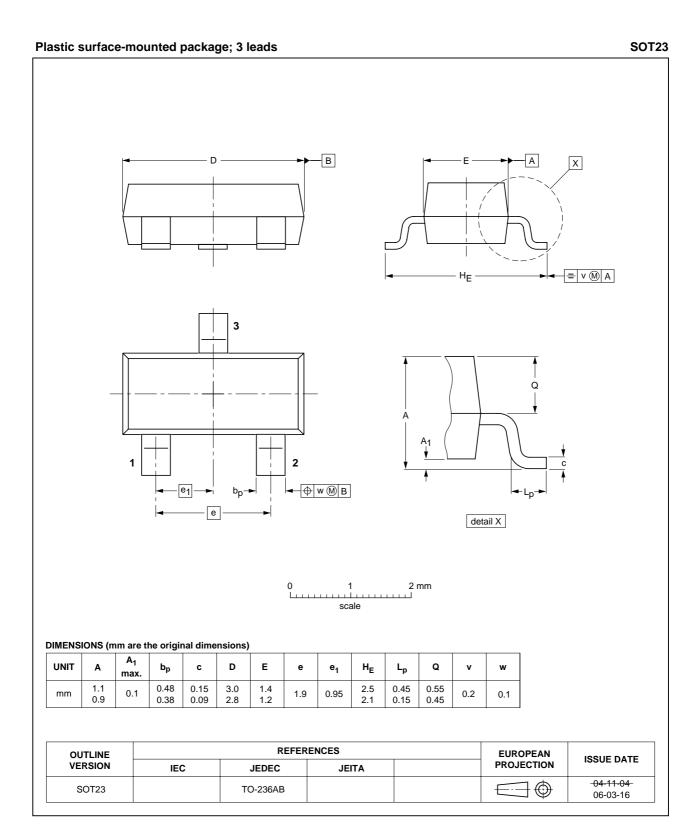


Fig 11. Package outline SOT23 (TO-236AB)

Product data sheet

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PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 10 k Ω

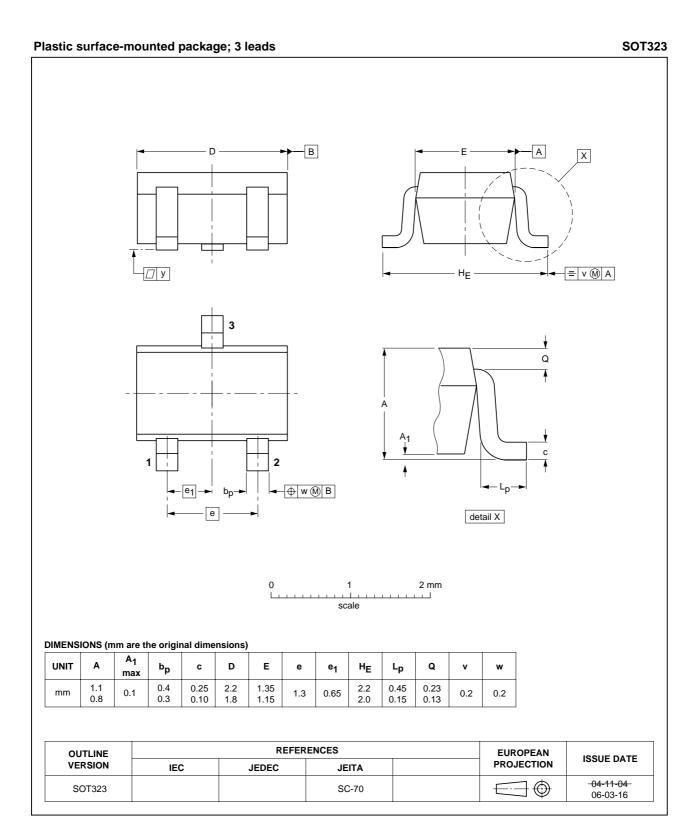


Fig 12. Package outline SOT323 (SC-70)

Product data sheet

PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 10 k Ω

Packing information

Table 9. **Packing methods**

Product data sheet

The indicated -xxx are the last three digits of the 12NC ordering code. [1]

Type number	Package	Description	Packing (Packing quantity		
			3000	5000	10000	
PDTA123YE	SOT416	4 mm pitch, 8 mm tape and reel	-115	-	-135	
PDTA123YK	SOT346	4 mm pitch, 8 mm tape and reel	-115	•	-135	
PDTA123YM	SOT883	2 mm pitch, 8 mm tape and reel	-	•	-315	
PDTA123YS	SOT54	bulk, straight leads	-	-412	-	
	SOT54A	tape and reel, wide pitch	•	•	-116	
		tape ammopack, wide patch	•	•	-126	
	SOT54 variant	bulk, delta pinning	-	-112	-	
PDTA123YT	SOT23	4 mm pitch, 8 mm tape and reel	-215	-	-235	
PDTA123YU	SOT323	4 mm pitch, 8 mm tape and reel	-115	-	-135	

^[1] For further information and the availability of packing methods, see Section 12.

PDTA123Y series

PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 10 k Ω

10. Revision history

Table 10. Revision history

	•						
Document ID	Release date	Data sheet status	Change notice	Supersedes			
PDTA123Y_SER_4	20090903	Product data sheet	-	PDTA123Y_SER_3			
Modifications:	fications: • This data sheet was changed to reflect the new company name NXP Sem including new legal definitions and disclaimers. No changes were made to content						
	 Figure 5 "Package outline SOT416 (SC-75)": updated 						
	 Figure 6 "Package outline SOT346 (SC-59A/TO-236)": updated 						
	Figure 11 "Page	ckage outline SOT23 (TO-	-236AB)": updated				
	 Figure 12 "Package outline SOT323 (SC-70)": updated 						
PDTA123Y_SER_3	20050405	Product data sheet	-	PDTA123YT_2			
PDTA123YT_2	20040611	Objective data sheet	-	PDTA123YT_1			
PDTA123YT_1	20040325	Objective data sheet	-	-			

11. Legal information

11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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12. Contact information

Product data sheet

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PDTA123Y series

PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 10 k Ω

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